Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	85	(257/364).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/11 12:54
L2	3	1 and ("Si.sub."$3"C.sub."$3 "Si.sub."$4C "Si:C" "C:Si" carbon carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 12:59
L3	310	257/407	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:17
L4	46	3 and ("Si.sub."$3"C.sub."$3 "Si.sub."$4C "Si:C" "C:Si" carbon carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:24
L5	2	3 and ((SiC silicon adj carbide).ti. "Si.sub."$3C "Si.sub."$4"C.sub."$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:24
L6	302	(257/76).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:24
L7	152	6 and ("Si.sub."$3"C.sub."$3 "Si.sub."$4C "Si:C" "C:Si" carbon carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:52
L8	27	6 and ((SiC silicon adj carbide).ti. "Si.sub."$3"C" "Si.sub."$4"C.sub."$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:26
L9	1	6 and (gate near4 ((SiC silicon adj carbide).ti. "Si.sub."$3"C" "Si.sub."$4"C.sub."$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 13:52
L10	1	3 and (gate near4 ((SiC silicon adj carbide).ti. "Si.sub."$3"C" "Si.sub."$4"C.sub."$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 13:51

L11	4564	((257/76) or (257/77) or (257/314) or (257/315) or (257/316) or (257/407) or (365/185.01)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/03/11 13:52
L12	936	11 and ("Si.sub."$3"C.sub."$3 "Si.sub."$4C "Si:C" "C:Si" carbon carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 13:52
L13	11	11 and (gate near4 ((SiC silicon adj carbide).ti. "Si.sub."$3"C" "Si.sub."$4"C.sub."$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 13:52
S1	13	(("4113515") or ("4473836") or ("5698869") or ("5858811") or ("5976926") or ("6031263") or ("6084248") or ("6093937") or ("6099574") or ("6130147") or ("6144581") or ("6163066") or ("6166401")).PN.	USPAT; USOCR	OR	OFF	2005/03/11 12:54
S2	13	(US-6144581-$ or US-6163066-$ or US-6166401-$ or US-4113515-$ or US-4473836-$ or US-5698869-$ or US-5858811-$ or US-5976926-$ or US-6031263-$ or US-6084248-$ or US-6093937-$ or US-6099574-$ or US-6130147-$).did.	USPAT	OR	OFF	2002/05/10 11:29
S3	1	hartstein.in. and low adj voltage adj memory.ti.	EPO	OR	ON	2002/05/10 11:28
S4	0	jp-63289960$-$.did.	USPAT	OR	OFF	2002/05/10 11:30
S5	0	jp-363289960$-$.did.	USPAT	OR	OFF	2002/05/10 11:30
S6	0	jp-0363289960$-$.did.	USPAT	OR	OFF	2002/05/10 11:34
S7	1	takashi.in. and carrier near6 silicon adj substrate	USPAT	OR	OFF	2002/05/10 11:36
S8	3	takashi.in. and carrier near6 silicon adj substrate	JPO	OR	OFF	2002/05/10 11:38
S9	38	diamond adj layer near6 process	DERWENT	OR	OFF	2002/05/10 11:39
S10	2	(diamond adj layer near6 process) and silicon adj carbide	DERWENT	OR	OFF	2002/05/10 11:45
S11	1	takashi.in. and ito.in. and igfet	EPO	OR	OFF	2002/05/10 11:45
S12	0	jp-063219172$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:47

S13	2	jp-63219172$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:15
S14	2	jp-63289960$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:49
S15	2	jp-01115162$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:49
S16	2	jp-63181473$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:50
S17	2	jp-62122275$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:51
S18	0	jp-404056769$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 11:52
S19	2	jp-04056769$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:02
S20	796	(257/77).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 14:04
S21	9	((257/77).CCLS.) and (x near12 silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:18
S22	489	silicon adj carbide and gate and x and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:19

S23	53	silicon adj carbide.ti,ab. and gate and x and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:26
S24	162	stoichiometric adj coefficient	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:26
S25	11	stoichiometric adj coefficient near x	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:26
S26	30	stoichiometric adj coefficient near12 x	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:28
S27	0	"si.sub.1-x.c.sub.x" and field adj effect adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:30
S28	0	"si.sub.1-x.c.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:29
S29	57	"si.sub.1-x" adj "c.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 12:31
S30	18	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 13:55
S31	15	"si.sub.1-x" adj "c.sub.x" and (mosfet or fet or nmosfet or pmosfet or field adj effect adj transistor or dtmosfet or (gate and (source or drain)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 13:57
S32	179	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c. 1-y") and x	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:07

S33	50	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c. 1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:15
S34	1	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c. 1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier adj energy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:10
S35	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c. 1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:24
S36	0	((257/77).CCLS.) and ("si.1-x. c.x. " or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:26
S37	0	((257/77).CCLS.) and ("si.1-x. c.x. " or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:20
S38	0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:20
S39	0	("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y") and x and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:20

S40	0	((257/77).CCLS.) and ("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:27
S41	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") and x and (source same drain) and gate and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:49
S42	30	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c. 1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) and x and (source same drain) and (mosfet or nmosfet or pmosfet or dtmosfet or cmosfet or fet or field adj effect adj transistor) and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:51
S43	53	((257/77).CCLS.) and (silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c. 1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and ("257"/$6.ccls. or "438"/$6. ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:52
S44	2616	(silicon carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si. y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and ("257"/$6.ccls. or "438"/$6. ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:53
S45	133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near12 gate) near12 x and ("257"/$6.ccls. or "438"/$6. ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:54
S46	133	(silicon adj carbide or "si.1-x. c.x." or "si.1-y. c.y." or ("si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and ("257"/$6.ccls. or "438"/$6. ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 14:55

S47	2	((silicon adj carbide or "si.1-x. c.x. " or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)") near6 gate) near12 x and ("257"/$6.ccls. or "438"/$6. ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 15:05
S48	0	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near6 gate) near12 x and ("257"/$6.ccls. or "438"/$6.ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 15:09
S49	0	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near12 gate) near12 (x or y or a or b) and ("257"/$6.ccls. or "438"/$6.ccls. or "361"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:35
S50	1	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near12 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 15:12
S51	684	(silicon adj carbide or sic or "si. 1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near12 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 15:13
S52	161	((silicon adj carbide or sic or "si. 1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near6 gate) and "257"/$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:42

S53	2	("6249020").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 16:24
S54	2	("6031263").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 17:09
S55	2	("6049110").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/10 17:09
S56	0	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near6 gate) and "257"/$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:33
S57	0	(("si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si. a.c.1-a" or "si.1-a.c.a" or "si.b.c. 1-b" or "si.1-b.c.b") near6 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:33

S58	51	(US-5451798-$ or US-6166319-$ or US-4113515-$ or US-4473836-$ or US-5698869-$ or US-5858811-$ or US-5976926-$ or US-6031263-$ or US-6084248-$ or US-6093937-$ or US-6099574-$ or US-6130147-$ or US-6144581-$ or US-6163066-$ or US-6166401-$ or US-5661312-$ or US-5719410-$ or US-5798548-$ or US-5801401-$ or US-6011279-$ or US-6049110-$ or US-6306691-$ or US-6313482-$ or US-6365919-$ or US-6249020-$ or US-6344663-$).did. or (US-5886368-$ or US-6383576-$ or US-4826778-$ or US-5039354-$ or US-5056897-$ or US-5159424-$ or US-5260560-$ or US-5369040-$).did. or (US-20010032997-$ or US-20010049183-$).did. or (EP-681333-$ or EP-291951-$). did. or (JP-04056769-$ or JP-62122275-$ or JP-63181473-$ or JP-01115162-$ or JP-63219172-$ or JP-63289960-$ or JP-56056677-$).did. or (JP-04056769-$ or JP-62122275-$ or EP-276002-$ or EP-291951-$ or JP-01115162-$ or JP-07115191-$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2002/05/10 18:34
S59	351	silicon near3 doped near6 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:36
S60	45	(silicon near3 doped near6 carbon) and ("257"/$6.ccls. or "438"/$6.ccls.) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:38
S61	4	((silicon near3 doped near6 carbon) near12 gate) and ("257"/$6.ccls. or "438"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:40
S62	5	((silicon near3 dop$3 near6 carbon) near12 gate) and ("257"/$6.ccls. or "438"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:41

S63	235	((carbon or silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and "257"/$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 18:43
S64	74	(((carbon or silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and "257"/$6.ccls.) not (((silicon adj carbide or sic or "si.1-x. c.x." or "si.1-y. c.y." or "si.x. c.1-x" or "si.y. c.1-y" or "si(x)c(1-x)" or "si(1-x)c(x)" or "si(a)c(1-a)" or "si(b)c(1-b)" or "si(1-a)c(a)" or "si(1-b)c(b)" or "si.a.c.1-a" or "si.1-a.c.a" or "si.b.c.1-b" or "si.1-b.c.b") near6 gate) and "257"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:13
S65	0	silicon-doped adj carbon adj (film or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:13
S66	0	si-doped adj carbon adj (film or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:14
S67	201	((c or carbon) near (si or silicon)) adj (film or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:15
S68	10092	((c or carbon) near6 (si or silicon)) near6 (film or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:16
S69	3434	(carbon near6 (si or silicon)) near6 (film or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 20:16

S70	118	(carbon near1 (si or silicon)) near3 (film or electrode) and ("257"/$6.ccls. or "438"/$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:21
S71	0	polysilicon/carbon near12 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:22
S72	0	"polysilicon/carbon" near12 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:22
S73	0	(polysilicon near1 carbon) near12 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:23
S74	1	(silicon near1 carbon) near12 gate adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:49
S75	6	p-doped adj silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:30
S76	7	P-dopant near12 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/10 21:49
S77	0	carbon adj doping adj2 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:21
S78	4	silicon adj doping adj2 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:27
S79	0	p-doped adj silicon adj carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:27

S80	7	p-doped adj2 silicon adj2 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:28
S81	1	(p-doped or p-doping) near12 silicon adj carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:31
S82	0	"si.sub.1-x.c.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:35
S83	57	"si.sub.1-x c.sub.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:43
S84	0	"si.sub.1-x c.sub.x" near20 (work adj function or workfunction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:43
S85	2	"si.sub.1-x c.sub.x" near20 (barrier or work adj function or workfunction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:48
S86	1	"si.sub.x c.sub.1-x" near20 (barrier or work adj function or workfunction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 16:49
S87	10	"si.sub.1-x c.sub.x" near20 (electrode or conductivity or conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 17:04
S88	1	("si.sub.1-x c.sub.x" or "si.sub.x c.sub.1-x" or "si.sub.1-y c.sub.y" or "si.sub.y c.sub.1-y") near20 electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 20:09
S89	0	resistivity near4 "si.sub.1-x. c.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 20:26

S90	965	(conductivity or resistivity) near12 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 20:39
S91	0	(conductivity or resistivity) near12 "si.sub.1-x c.x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 21:10
S92	8	barrier adj energy near12 silicon adj dioxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 21:14
S93	0	barrier adj energy near12 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 21:20
S94	108	barrier adj energy.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 21:23
S95	2	barrier adj energy near12 (sic or "si.sub.1-x. c.x" or silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/11 21:24
S96	21	(resistivity or conductivity) near12 (silicon adj carbide or "si.sub.1-x. c.sub.x" or "si.sub.x. c.sub.1-x") near12 x	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:26
S97	17	barrier adj energy near12 gate near12 insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:07
S98	3	("5661312").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 12:10
S99	0	("floatingadjgateandcontroladjgate andsiliconadjdioxideand(sicorsilico nadjcarbide)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 12:10

S10 0	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:11
S10 1	0	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and photodetection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:12
S10 2	30	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:21
S10 3	18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:21
S10 4	18	floating adj gate and control adj gate and silicon adj dioxide and (sic or silicon adj carbide) and memory and (barrier adj energy or potential adj barrier or tunneling adj barrier or interface adj barrier or barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 12:23
S10 5	3	("5886368").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 17:44
S10 6	3	("5661312").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 17:46
S10 7	46061	polycrystalline near12 silicon carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 17:48
S10 8	13	polycrystalline near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 17:50

S10 9	22	(polycrystalline or monocrystalline) near12 silicon adj carbide and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 17:51
S11 0	4	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate and (mosfet or fet or nmosfet or pmosfet or cmosfet or field ajd effect adj transistor) and (memory or photodetect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 17:52
S11 1	24	(polycrystalline or monocrystalline) near12 silicon adj carbide near12 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:16
S11 2	3	("5369040").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 18:17
S11 3	10	floating adj gate near12 control adj gate and photodetect$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:30
S11 4	0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect$3 and (mosfet or cmos or cmosfet or nmos or nmosfet or pmos or pmosfet or transistor or field adj effect)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:31
S11 5	0	floating adj gate near12 control adj gate near12 silicon adj carbide and photodetect$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:31
S11 6	0	floating adj gate near12 control adj gate near12 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:32
S11 7	2	floating adj gate near12 control adj gate near12 (sic or silicon adj carbide or "si.sub.1-x. c.sub.x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/12 18:56

S11 8	2	("5989958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 19:00
S11 9	3	("5801401").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 19:33
S12 0	2	("5808336").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 19:43
S12 1	3	("5801401").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/12 19:43
S12 2	3	("4473836").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/13 10:06
S12 3	2	("5808336").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/13 10:11
S12 4	3	("5801401").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/13 11:25
S12 5	0	floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 11:26
S12 6	41	floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 11:27

S12 7	41	floating adj gate and control adj gate and source same drain and silicon adj carbide and silicon adj substrate and channel and (memory or photodetect$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 12:16
S12 8	74	crystalline near12 floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 12:16
S12 9	37	crystalline near3 floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 13:21
S13 0	5	(("5661312") or ("5798548") or ("5989958") or ("5369040") or ("5557122")).PN.	USPAT; USOCR	OR	OFF	2002/05/13 16:23
S13 1	47	hamakawa.in. and carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 16:13
S13 2	24	hamakawa.in. and carbide	JPO	OR	ON	2002/05/13 16:13
S13 3	1	("5808336").PN.	USPAT; USOCR	OR	OFF	2002/05/13 17:16
S13 4	52	(("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.	USPAT; USOCR	OR	OFF	2002/05/13 17:30

| S13 5 | 6 | (((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c.sub.1-x" or "si.sub.y c.sub.1-y" or silicon carbide or sic) and source and drain and floating adj gate and control adj gate and silicon adj dioxide | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2002/05/13 18:18 |

S13 6	0	((("4460670") or ("4462150") or ("4507673") or ("4657699") or ("4738729") or ("4768072") or ("4769686") or ("4841349") or ("4849797") or ("4893273") or ("5049950") or ("5111430") or ("5145741") or ("5235195") or ("5260593") or ("5293560") or ("5298796") or ("5369040") or ("5371383") or ("5407845") or ("5415126") or ("5449941") or ("5455432") or ("5465249") or ("5477485") or ("5508543") or ("5530581") or ("5557114") or ("5562769") or ("5580380") or ("5604357") or ("5623442") or ("5629222") or ("5654208") or ("5670790") or ("5714766") or ("5719410") or ("5740104") or ("5754477") or ("5786250") or ("5789276") or ("5801401") or ("5846859") or ("5877041") or ("5886368") or ("5886379") or ("5898197") or ("5907775") or ("6018166") or ("6031263") or ("6034001") or ("6075259")).PN.) and ("si.sub.1-x. c.sub.x" or "si.sub.1-y. c.sub.y" or "si.sub.x c. sub.1-x" or "si.sub.y c.sub.1-y") and source and drain and floating adj gate and control adj gate and silicon adj dioxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 20:34
S13 7	588	(257/77).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/13 20:34
S13 8	118	(257/153).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/13 20:34
S13 9	402	(257/314).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/13 20:39
S14 0	782	(257/315).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/13 20:39
S14 1	943	(257/316).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2002/05/13 20:40
S14 2	2311	((257/77).CCLS.) or ((257/153). CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 20:40

S14 3	357	(((257/77).CCLS.) or ((257/153). CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316). CCLS.)) and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 20:44
S14 4	90	(((257/77).CCLS.) or ((257/153). CCLS.) or ((257/314).CCLS.) or ((257/315).CCLS.) or ((257/316). CCLS.)) and (silicon adj carbide near15 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/13 21:12
S14 5	2	("5989958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/13 21:12

| S14 6 | 115 | (US-5449941-$ or US-5455432-$ or US-5039354-$ or US-5056897-$ or US-5159424-$ or US-5260560-$ or US-5369040-$ or US-5451798-$ or US-5734181-$ or US-6166319-$ or US-6383576-$ or US-5801401-$ or US-5989958-$ or US-6344663-$ or US-4113515-$ or US-4473836-$ or US-5698869-$ or US-5858811-$ or US-5976926-$ or US-6031263-$ or US-6084248-$ or US-6093937-$ or US-6099574-$ or US-6130147-$ or US-6144581-$ or US-6163066-$).did. or (US-6166401-$ or US-5465249-$ or US-4451391-$ or US-6309907-$ or US-5061976-$ or US-5625217-$ or US-5661312-$ or US-5798548-$ or US-6011279-$ or US-6049110-$ or US-6249020-$ or US-6306691-$ or US-6313482-$ or US-6365919-$ or US-5719410-$ or US-5886368-$ or US-4826778-$ or US-6351411-$ or US-5557114-$ or US-5562769-$ or US-5580380-$ or US-5604357-$ or US-5623442-$ or US-5629222-$ or US-5654208-$ or US-5670790-$ or US-5714766-$).did. or (US-5740104-$ or US-5754477-$ or US-5786250-$ or US-5789276-$ or US-5846859-$ or US-5877041-$ or US-5886379-$ or US-5907775-$ or US-6018166-$ or US-6034001-$ or US-6075259-$ or US-5557122-$ or US-5866930-$ or US-5898197-$ or US-5808336-$ or US-5393999-$ or US-5539217-$ or US-4460670-$ or US-4462150-$ or US-4507673-$ or US-4657699-$ or US-4738729-$ or US-4768072-$ or US-4769686-$ or US-4841349-$ or US-4849797-$ or US-4893273-$).did. or (US-5049950-$ or US-5111430-$ or US-5145741-$ or US-5235195-$ or US-5260593-$ or US-5293560-$ or US-5298796-$ or US-5371383-$ or US-5407845-$ or US-5415126-$ or US-5508543-$ or US-5530581-$ or US-5477485-$).did. or (US-20010032997-$ or US-20010049183-$ or US-20020024050-$ or US-20020017647-$).did. or (EP-291951-$ or EP-681333-$). did. or (JP-62122275-$ or JP-63181473-$ or JP-01115162-$ or JP-63219172-$ or JP-04056769-$ or JP-63289960-$ or JP-57126175-$ or JP-04061170-$ or JP-56056677-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2002/05/14 08:24 |

| S14 7 | 1 | ((US-5449941-$ or US-5455432-$ or US-5039354-$ or US-5056897-$ or US-5159424-$ or US-5260560-$ or US-5369040-$ or US-5451798-$ or US-5734181-$ or US-6166319-$ or US-6383576-$ or US-5801401-$ or US-5989958-$ or US-6344663-$ or US-4113515-$ or US-4473836-$ or US-5698869-$ or US-5858811-$ or US-5976926-$ or US-6031263-$ or US-6084248-$ or US-6093937-$ or US-6099574-$ or US-6130147-$ or US-6144581-$ or US-6163066-$).did. or (US-6166401-$ or US-5465249-$ or US-4451391-$ or US-6309907-$ or US-5061976-$ or US-5625217-$ or US-5661312-$ or US-5798548-$ or US-6011279-$ or US-6049110-$ or US-6249020-$ or US-6306691-$ or US-6313482-$ or US-6365919-$ or US-5719410-$ or US-5886368-$ or US-4826778-$ or US-6351411-$ or US-5557114-$ or US-5562769-$ or US-5580380-$ or US-5604357-$ or US-5623442-$ or US-5629222-$ or US-5654208-$ or US-5670790-$ or US-5714766-$).did. or (US-5740104-$ or US-5754477-$ or US-5786250-$ or US-5789276-$ or US-5846859-$ or US-5877041-$ or US-5886379-$ or US-5907775-$ or US-6018166-$ or US-6034001-$ or US-6075259-$ or US-5557122-$ or US-5866930-$ or US-5898197-$ or US-5808336-$ or US-5393999-$ or US-5539217-$ or US-4460670-$ or US-4462150-$ or US-4507673-$ or US-4657699-$ or US-4738729-$ or US-4768072-$ or US-4769686-$ or US-4841349-$ or US-4849797-$ or US-4893273-$).did. or (US-5049950-$ or US-5111430-$ or US-5145741-$ or US-5235195-$ or US-5260593-$ or US-5293560-$ or US-5298796-$ or US-5371383-$ or US-5407845-$ or US-5415126-$ or US-5508543-$ or US-5530581-$ or US-5477485-$).did. or (US-20010032997-$ or US-20010049183-$ or US-20020024050-$ or US-20020017647-$).did. or (EP-291951-$ or EP-681333-$). did. or (JP-62122275-$ or JP-63181473-$ or JP-01115162-$ or JP-63219172-$ or JP-04056769-$ or JP-63289960-$ or JP-57126175-$ or JP-04061170-$ or JP-56056677-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2002/05/14 08:34 |

S148	799	(257/77).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/14 08:53
S149	2	("5989958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/14 10:54
S150	469	(257/314).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/14 09:08
S151	467	((257/314).CCLS.) not ((257/77). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 09:24
S152	1816	257/315	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 09:24
S153	1577	(257/315 not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 09:26
S154	1375	(257/316).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/14 10:54
S155	858	(((((257/316).CCLS.) not 257/315) not (((257/314).CCLS.) not ((257/77).CCLS.))) not ((257/77). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 10:55
S156	0	("jp-3222367$-$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/14 12:45

S157	2	jp-03222367$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:46
S158	13	jp-0224431$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:46
S159	2	jp-06224431$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:47
S160	10	jp-302828$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:48
S161	2	jp-06302828$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:48
S162	2	jp-07226507$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:49
S163	2	jp-08255878$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:50
S164	0	jp-08255878TR$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:50
S165	0	jp-08255878-TR$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:50
S166	2	jp-60184681$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:52

S16 7	2	jp-60242678$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 12:52
S16 8	4	method adj2 using.clm. and optical adj switch.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/14 13:29
S16 9	714	(257/295).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 13:13
S17 0	0	("mram.ti,ab.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 13:13
S17 1	276	mram.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 13:21
S17 2	988	((257/295).CCLS.) or mram.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 13:21
S17 3	873	magnetic adj memory adj device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 13:32
S17 4	4	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 13:38
S17 5	8	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 14:56
S17 6	1	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and (ferrimagnetic or ferrimagnet) adj2 (layer or film) same orient$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 15:06

S17 7	1846	((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 17:14
S17 8	2	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 15:51
S17 9	1	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 15:59
S18 0	0	(((257/295).CCLS.) or mram.ti,ab. or (magnetic adj memory adj device)) and data adj (layer or film) near15 (magnetization or magnetisation or magnetized or magnetised) near15 (turn or turning or orientation or orient or oriented) and coercivity and ferrimagnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 17:01
S18 1	719	((257/295).CCLS.) or (magnetic adj memory adj device) and af adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 17:17
S18 2	44	(365/172).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 17:35
S18 3	283	(365/173).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 17:35
S18 4	804	((365/171) or (365/172) or (365/173)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 18:02

S18 5	0	(((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (data adj storage near3 (layer or film))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 18:08
S18 6	4	(((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity	US-PGPUB; USPAT	OR	ON	2002/05/15 18:10
S18 7	4	(((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	US-PGPUB; USPAT	OR	ON	2002/05/15 19:32
S18 8	0	(((365/171) or (365/172) or (365/173)).CCLS.) and ((synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) near6 (layer or film))	US-PGPUB; USPAT	OR	ON	2002/05/15 18:31
S18 9	0	(((365/171) or (365/172) or (365/173)).CCLS.) and (synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic)	US-PGPUB; USPAT	OR	ON	2002/05/15 18:31
S19 0	23	(synthetic adj ferrimagnetic or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory)	US-PGPUB; USPAT	OR	ON	2002/05/15 18:36
S19 1	2	(synthetic adj (ferrimagnet or ferrimagnetic) or sf or artificial adj ferrimagnetic) and (mram or magnetic adj memory).ti,ab.	US-PGPUB; USPAT	OR	ON	2002/05/15 18:38
S19 2	4	(((365/171) or (365/172) or (365/173)).CCLS.) and (antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	US-PGPUB; USPAT	OR	ON	2002/05/15 19:44
S19 3	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	US-PGPUB; USPAT	OR	ON	2002/05/15 19:46

S19 4	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity and (angle or orient or orientation or oriented or turn or turned or turning or rotate or rotated or rotation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 19:48
S19 5	4	(antiferrimagnetic or femn or af) adj (layer of film) and (magnetic adj memory) and coercivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 19:48
S19 6	17	(antiferrimagnetic or femn or af) and (magnetic adj memory) and coercivity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 19:51
S19 7	8934	(antiferrimagnetic or femn or af) and (hs mtj or hard-soft adj mtj)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 19:52
S19 8	1	(antiferrimagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 21:17
S19 9	1	"5966012".PN.	USPAT	OR	OFF	2002/05/15 20:52
S20 0	1	"5841692".PN.	USPAT	OR	OFF	2002/05/15 20:55
S20 1	1	"5801984".PN.	USPAT	OR	OFF	2002/05/15 20:56
S20 2	1	"5055158".PN.	USPAT	OR	OFF	2002/05/15 20:57
S20 3	1	"5055158".PN.	USPAT	OR	OFF	2002/05/15 20:58
S20 4	1	(antiferromagnetic or femn or af) and (hs adj mtj or hard-soft adj mtj)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 21:24
S20 5	2	("5605958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 21:24

S20 6	3	("5650958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/15 22:05
S20 7	77	magnetic adj memory and spacer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 22:29
S20 8	0	magnetic adj memory and (spacer adj layer near12 sf)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 22:30
S20 9	77	magnetic adj memory and spacer adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/15 22:48
S21 0	7	magnetic adj memory and (spacer adj layer near5 antiferromagnetic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 07:45
S21 1	3	magnetic adj memory and (spacer adj layer near5 antiferromagnetic) and (spacer near12 different)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 08:01
S21 2	0	(spacer near12 antiferromagnetic near12 different) and magnetic adj2 memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 08:02
S21 3	5	spacer near12 antiferromagnetic near12 different	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 08:45
S21 4	295	(365/158).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:45

S215	602	(365/171).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:46
S216	44	(365/172).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:46
S217	283	(365/173).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:46
S218	3429	(365/174).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:46
S219	431	(257/30).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/05/16 08:47
S220	4807	((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 08:47
S221	179	spacer and coercivity and antiferromagnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 08:48
S222	11	(((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172).CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30).CCLS.)) and (spacer and coercivity and antiferromagnetic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 13:56

S22 3	5	(((((365/158).CCLS.) or ((365/171).CCLS.) or ((365/172). CCLS.) or ((365/173).CCLS.) or ((365/174).CCLS.) or ((257/30). CCLS.)) and (spacer and coercivity and antiferromagnetic)) and @pd<"20000104"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 14:30
S22 4	0	mtj adj mr and world adj line and bottom adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 14:31
S22 5	0	mtj adj mr and world adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 14:32
S22 6	1	mtj adj mr and word adj line	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 14:33
S22 7	7	"6114719"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 15:30
S22 8	3	mtj and (current near12 (magnetization or magnetized)) near12 (perpendicular or orthogonal)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:37
S22 9	0	"not pinned" and (mram or mtj)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:44
S23 0	0	"not pinned" and (mram or mtj or magneto-resistive or af adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:45
S23 1	178	(hard same soft) and (mram or mtj or magneto-resistive or af adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:47
S23 2	0	(soft-soft) and (mram or mtj or magneto-resistive or af adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:47

S23 3	0	soft-soft and (mtj or mram or magneto-resistive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:49
S23 4	11	soft-soft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:50
S23 5	0	soft-soft and magnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 16:50
S23 6	3	mtj and second adj free	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 20:54
S23 7	17	(spacer near12 (ru or ruthenium)) near12 (af adj layer reference adj layer or data adj layer or sens$3 adj layer or pinned adj2 layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/05/16 22:40
S23 8	3	(("5640343") or ("6269018") or ("5966012")).PN.	USPAT; USOCR	OR	OFF	2002/05/16 23:13
S23 9	2	"903452".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 11:23
S24 0	2	("5989958").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/04 12:57
S24 1	0	jp-03571261$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 12:58
S24 2	8	hamakawa.in. and silicon and carbide and semiconductor	JPO	OR	ON	2002/11/04 13:00
S24 3	2	"3571261"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 12:59

S244	1	"carbide/amorophous".ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 15:49
S245	0	optoelectric adj conversion and electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:04
S246	329	optoelectric adj conversion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:04
S247	2724	electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:04
S248	0	optoelectric adj conversion near12 affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:05
S249	32	optoelectric adj conversion near12 efficiency	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:06
S250	4	optoelectric adj conversion near12 efficiency and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/04 18:07
S251	3404	((257/77) or (257/314) or (257/315) or (257/316)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/05 11:44
S252	14	(((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and breakdown adj voltage near15 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/05 11:46
S253	1	(((257/77) or (257/314) or (257/315) or (257/316)).CCLS.) and electron adj affinity near15 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/05 11:47

S25 4	2	("6104054").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/05 14:24
S25 5	8	(("5661312") or ("5798548") or ("5989958") or ("5808336") or ("5369040") or ("5557122") or ("5393999") or ("5734181")).PN.	USPAT; USOCR	OR	OFF	2003/01/27 10:34
S25 6	0	jp-357126175$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 10:38
S25 7	2	jp-57126175$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 10:40
S25 8	2	jp-02203564$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/01/27 10:40
S25 9	13	(US-6084248-$ or US-6031263-$ or US-5976926-$ or US-5858811-$ or US-5698869-$ or US-4473836-$ or US-4113515-$ or US-6130147-$ or US-6144581-$ or US-6099574-$ or US-6093937-$ or US-6166401-$ or US-6163066-$).did.	USPAT	OR	OFF	2003/03/21 13:50
S26 0	57	hamakawa.in. and conversion	USPAT; JPO	OR	OFF	2003/03/21 13:51
S26 1	0	hamakawa.in. and conversion and optoelectronic	JPO	OR	OFF	2003/03/21 13:51
S26 2	1	hamakawa.in. and conversion and heterojunction	JPO	OR	OFF	2003/03/21 13:52
S26 3	31	hamakawa.in. and conversion	JPO	OR	OFF	2003/03/21 13:52

S26 4	141	(US-5449941-$ or US-6383576-$ or US-6166319-$ or US-5451798-$ or US-5734181-$ or US-5260560-$ or US-5886379-$ or US-5786250-$ or US-5877041-$ or US-5846859-$ or US-5789276-$ or US-5754477-$ or US-5740104-$ or US-5670790-$ or US-5714766-$ or US-5654208-$ or US-5623442-$ or US-5580380-$ or US-5604357-$ or US-5562769-$ or US-5557114-$ or US-5530581-$ or US-5477485-$ or US-5455432-$ or US-5407845-$ or US-5415126-$).did. or (US-5298796-$ or US-5293560-$ or US-5260593-$ or US-5235195-$ or US-5145741-$ or US-5111430-$ or US-5049950-$ or US-4893273-$ or US-4841349-$ or US-4769686-$ or US-4738729-$ or US-4657699-$ or US-4462150-$ or US-4460670-$ or US-6002143-$ or US-5852306-$ or US-4849797-$ or US-5369040-$ or US-5039354-$ or US-5159424-$ or US-5056897-$ or US-4826778-$ or US-5886368-$ or US-5719410-$ or US-5371383-$ or US-6236590-$ or US-6166948-$).did. or (US-5793697-$ or US-5640343-$ or US-6205052-$ or US-6178112-$ or US-6197439-$ or US-6108177-$ or US-5408377-$ or US-6365919-$ or US-6313482-$ or US-6306691-$ or US-6249020-$ or US-6018166-$ or US-6133587-$ or US-6121633-$ or US-6075259-$ or US-6049110-$ or US-6011279-$ or US-5798548-$ or US-5661312-$ or US-5539217-$ or US-5465249-$ or US-5323040-$ or US-4507673-$ or US-5625217-$ or US-5061976-$ or US-6344663-$ or US-6180958-$).did. or (US-5989958-$ or US-5801401-$ or US-5393999-$ or US-5629222-$ or US-6309907-$ or US-4768072-$ or US-4451391-$ or US-6351411-$ or US-5898197-$ or US-5508543-$ or US-5808336-$ or US-5866930-$ or US-5557122-$ or US-6034001-$ or US-5907775-$ or US-6166401-$ or US-6163066-$ or US-6144581-$ or US-6093937-$ or US-6099574-$ or US-6130147-$ or US-6031263-$ or US-6084248-$ or US-5976926-$ or US-5698869-$ or US-4113515-$ or US-4473836-$).did. or (US-5858811-$).did. or US-20020017647-$ or US-20020036331-$ or US-20020041514-$ or	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/03/25 11:00

| S26 5 | 1 | ((US-5449941-$ or US-6383576-$ or US-6166319-$ or US-5451798-$ or US-5734181-$ or US-5260560-$ or US-5886379-$ or US-5786250-$ or US-5877041-$ or US-5846859-$ or US-5789276-$ or US-5754477-$ or US-5740104-$ or US-5670790-$ or US-5714766-$ or US-5654208-$ or US-5623442-$ or US-5580380-$ or US-5604357-$ or US-5562769-$ or US-5557114-$ or US-5530581-$ or US-5477485-$ or US-5455432-$ or US-5407845-$ or US-5415126-$).did. or (US-5298796-$ or US-5293560-$ or US-5260593-$ or US-5235195-$ or US-5145741-$ or US-5111430-$ or US-5049950-$ or US-4893273-$ or US-4841349-$ or US-4769686-$ or US-4738729-$ or US-4657699-$ or US-4462150-$ or US-4460670-$ or US-6002143-$ or US-5852306-$ or US-4849797-$ or US-5369040-$ or US-5039354-$ or US-5159424-$ or US-5056897-$ or US-4826778-$ or US-5886368-$ or US-5719410-$ or US-5371383-$ or US-6236590-$ or US-6166948-$).did. or (US-5793697-$ or US-5640343-$ or US-6205052-$ or US-6178112-$ or US-6197439-$ or US-6108177-$ or US-5408377-$ or US-6365919-$ or US-6313482-$ or US-6306691-$ or US-6249020-$ or US-6018166-$ or US-6133587-$ or US-6121633-$ or US-6075259-$ or US-6049110-$ or US-6011279-$ or US-5798548-$ or US-5661312-$ or US-5539217-$ or US-5465249-$ or US-5323040-$ or US-4507673-$ or US-5625217-$ or US-5061976-$ or US-6344663-$ or US-6180958-$).did. or (US-5989958-$ or US-5801401-$ or US-5393999-$ or US-5629222-$ or US-6309907-$ or US-4768072-$ or US-4451391-$ or US-6351411-$ or US-5898197-$ or US-5508543-$ or US-5808336-$ or US-5866930-$ or US-5557122-$ or US-6034001-$ or US-5907775-$ or US-6166401-$ or US-6163066-$ or US-6144581-$ or US-6093937-$ or US-6099574-$ or US-6130147-$ or US-6031263-$ or US-6084248-$ or US-5976926-$ or US-5698869-$ or US-4113515-$ or US-4473836-$).did. or (US-5858811-$).did. or (US-20020017647-$ or US-20020036331-$ or US-20020041514-$ or | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2003/03/25 11:00 |

S266	1	("4460670").PN.	USPAT; USOCR	OR	OFF	2003/03/25 17:05
S267	1	("4462150").PN.	USPAT; USOCR	OR	OFF	2003/03/25 17:05
S268	10	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:38
S269	11	(transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:35
S270	1	((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:35
S271	8	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and "257"/$9.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:40
S272	0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y)) and "257"/$9.ccls.) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:39
S273	10	gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 17:40
S274	0	(gate near12 ("Si.sub.1-x C.sub.x" silicon adj carbide near12 (x or y))) not ((transistor MOS MOSFET) and gate near12 ("Si.sub.1-x C.sub.x" "Si.sub.x C.sub.1-x" "Si.sub.1-y C.sub.y" "Si.sub.y C.sub.1-y" silicon adj carbide near12 (x or y)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/18 18:18

S27 5	2	("5661312").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 09:13
S27 6	0	("jp-57125175$-$.did.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 09:14
S27 7	0	jp-57125175$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 09:14
S27 8	2	jp-57126175$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:49
S27 9	229	barrier near6 gate and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 09:35
S28 0	5	barrier near6 gate near6 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:02
S28 1	1	"5506421".PN.	USPAT	OR	OFF	2003/08/19 09:37
S28 2	1	"5495124".PN.	USPAT	OR	OFF	2003/08/19 09:39
S28 3	1	"5451797".PN.	USPAT	OR	OFF	2003/08/19 09:39
S28 4	1	"5396085".PN.	USPAT	OR	OFF	2003/08/19 09:43
S28 5	1	"5393999".PN.	USPAT	OR	OFF	2003/08/19 09:45
S28 6	15	gate near6 breakdown near6 (silicon adj carbide "Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C. sub.1-x")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:12

S287	304	"Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:13
S288	12	("Si.sub.1-x" adj "C.sub.x" "Si.sub.x" adj "C.sub.1-x") and gate near6 breakdown	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:14
S289	2	("5369040").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:58
S290	0	("MOSadjphotodetector.ti,ab.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 10:58
S291	8	MOS adj photodetector.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 11:50
S292	17	gate near6 polysilicon near6 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:12
S293	1	"4963953".PN.	USPAT	OR	OFF	2003/08/19 12:03
S294	1	"4780394".PN.	USPAT	OR	OFF	2003/08/19 12:04
S295	1	"4352237".PN.	USPAT	OR	OFF	2003/08/19 12:04
S296	1	"4189826".PN.	USPAT	OR	OFF	2003/08/19 12:04
S297	4	("3497773" | "3622382" | "3728590" | "3896485").PN.	USPAT	OR	OFF	2003/08/19 12:07
S298	43	"3896485".URPN.	USPAT	OR	OFF	2003/08/19 12:07
S299	1	MOS adj photodetector.ti,ab,clm. and source and channel and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:13

S300	1	(MOS MOSFET) adj photodetector. ti,ab,clm. and source and channel and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:16
S301	395	photodetector.ti,ab,clm. and source and channel and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:17
S302	100	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:17
S303	0	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (sic silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:19
S304	1	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 12:23
S305	7	photodetector.ti,ab,clm. and source near20 channel near20 drain near20 gate near20 (silicon polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 13:12
S306	2	("5808336").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 13:13
S307	51	floating adj gate and photodetector and source and drain and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 13:55
S308	65	double-poly near12 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 15:12
S309	0	"4963953".PN.	USPAT	OR	OFF	2003/08/19 15:07

S310	21	(("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907")).PN.	USPAT; USOCR	OR	OFF	2003/08/19 15:29
S311	9	((("3792465") or ("4118795") or ("4384349") or ("4816883") or ("4897710") or ("5317535") or ("5366713") or ("5388069") or ("5424993") or ("5438544") or ("5441901") or ("5467306") or ("5493140") or ("5672889") or ("5828101") or ("5861346") or ("5912837") or ("5926740") or ("6297521") or ("6307775") or ("6309907")).PN.) and (silicon adj carbide or carbon near3 (polysilicon silicon))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:01
S312	122	silicon adj carbide and monocrystalline and power adj2 (MOS MOSFET device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:02
S313	59	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:02
S314	13	silicon adj carbide near12 monocrystalline and power adj2 (MOS MOSFET device).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:04
S315	1430	silicon adj carbide near6 (MOS MOSFET device).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:05
S316	111	silicon adj carbide near6 power near6 (MOS MOSFET device).ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:05

S31 7	55	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:05
S31 8	6	silicon adj carbide near6 power near6 (MOS MOSFET).ti,ab,clm. and monocrystalline near6 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:15
S31 9	1811	amorphous adj silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:16
S32 0	73	amorphous adj silicon adj carbide and grain adj size	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:16
S32 1	2	amorphous adj silicon adj carbide near12 grain adj size	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:32
S32 2	23	epitaxial$2 near12 silicon adj carbide near12 method and (monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:34
S32 3	5	epitaxial$2 near12 silicon adj carbide near12 method near12 (monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:35
S32 4	463	method near12 epitaxial$2 near12 (monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:38
S32 5	112	method near12 epitaxial$2 near12 (monocrystal monocrystalline) and "117"/$6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:59
S32 6	112	method near12 epitaxial$2 near12 crystallinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 16:59

S32 7	0	method near12 epitaxial$2 near12 crystallinity and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:00
S32 8	0	method near12 epitaxial$2 near12 ensur$3 near12 crystallinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:00
S32 9	49	monocrystalline near4 silicon adj carbide and power.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:01
S33 0	2	monocrystalline near4 silicon adj carbide near6 breakdown and power.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:02
S33 1	2	("5,449,925").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:02
S33 2	2	("5449925").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:03
S33 3	1	(("5449925").PN.) and epitaxial$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:05
S33 4	10	epitaxial$3 near6 grow$3 near6 monocrystalline near6 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:08
S33 5	14	grow$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:08
S33 6	3	method near6 grow$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:09

S33 7	1	method near6 grow$3 near6 monocrystalline near6 silicon adj carbide.ti,ab,clm. and power.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:09
S33 8	16	method near6 (growth growing) near6 (monocrystalline monocrystal) near12 (silicon adj carbide sic)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:11
S33 9	13	method near6 (growth growing) near6 (monocrystalline monocrystal) near12 (silicon adj carbide sic) and epitaxial$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:20
S34 0	2	jp-57126175$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:25
S34 1	13	epitaxy near6 (grain crystal) adj size	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:39
S34 2	4	(work adj function workfunction) near12 crystallinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:41
S34 3	184995	(work adj function workfunction) near12 silicon carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:41
S34 4	15	(work adj function workfunction) near12 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:43
S34 5	15	(work adj function workfunction) near12 crystalline near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:58
S34 6	0	("carbonadjgate").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:59

S34 7	9657	gate adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 17:59
S34 8	0	carbon adj gate and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 18:00
S34 9	23	carbon adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 18:00
S35 0	19	carbon adj gate and ("257"/$9. ccls. "117"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 18:03
S35 1	14	"carbon gate" and ("257"/$9.ccls. "117"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/19 18:04
S35 2	63	("si.sub.x" adj "c.sub.1-x" or "si. sub.1-x" adj "c.sub.x") and (energy adj gap or band adj energy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 10:00
S35 3	132	nanocrystalline and amorphous and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 11:47
S35 4	0	nanocrystalline near20 amorphous near20 silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 11:47
S35 5	4	nanocrystalline same amorphous same silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 12:23

| S35 6 | 157 | (US-6121633-$ or US-6133587-$ or US-6297521-$ or US-6306691-$ or US-6313482-$ or US-6249020-$ or US-6365919-$ or US-6075259-$ or US-5323040-$ or US-6130147-$ or US-5698869-$ or US-5465249-$ or US-4113515-$ or US-4849797-$ or US-4507673-$ or US-6031263-$ or US-5858811-$ or US-6011279-$ or US-6049110-$ or US-5976926-$ or US-4473836-$ or US-5734181-$ or US-6383576-$ or US-5449941-$ or US-5393999-$ or US-5629222-$).did. or (US-5801401-$ or US-6166401-$ or US-6018166-$ or US-5989958-$ or US-6180958-$ or US-6344663-$ or US-5886368-$ or US-5039354-$ or US-4826778-$ or US-6163066-$ or US-6084248-$ or US-6099574-$ or US-5260560-$ or US-5159424-$ or US-5056897-$ or US-5451798-$ or US-5369040-$ or US-6166319-$ or US-6093937-$ or US-6144581-$ or US-5539217-$ or US-5371383-$ or US-5719410-$ or US-5661312-$ or US-5672889-$ or US-5798548-$ or US-5506421-$).did. or (US-6562131-$ or US-6547877-$ or US-6562130-$ or US-6537371-$ or US-5030580-$ or US-4189826-$ or US-5932902-$ or US-4598305-$ or US-5449925-$ or US-5441901-$ or US-6236590-$ or US-4462150-$ or US-4460670-$ or US-4657699-$ or US-5604357-$ or US-5580380-$ or US-5623442-$ or US-5654208-$ or US-5670790-$ or US-5714766-$ or US-5740104-$ or US-5754477-$ or US-5786250-$ or US-5789276-$ or US-5846859-$ or US-5877041-$ or US-5907775-$).did. or (US-6034001-$ or US-5886379-$ or US-5557122-$ or US-5866930-$ or US-5808336-$ or US-5508543-$ or US-5898197-$ or US-6351411-$ or US-6178112-$ or US-6205052-$ or US-6197439-$ or US-5640343-$ or US-5793697-$ or US-6166948-$ or US-6307775-$ or US-4451391-$ or US-4768072-$ or US-6309907-$ or US-5061976-$ or US-5625217-$ or US-6002143-$ or US-5852306-$ or US-6108177-$ or US-5408377-$ or US-5145741-$ or US-5235195-$ or US-5260593-$).did. or (US-5293560-$ or US-5298796-$ or US-5407845-$ or US-5415126-$ or US-5455432-$ or US-5477485-$ or US-5530581-$ or US-5557114-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2003/08/20 12:07 |

S35 7	0	ultra-amorphous near6 nanocrystalline	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/08/20 12:08
S35 8	0	ultra-amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/08/20 12:08
S35 9	0	ultra adj amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/08/20 12:08
S36 0	26	carbon adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 12:46
S36 1	4	(carbon adj gate "carbon gate") and float$3 near4 gate and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 13:04
S36 2	2	("4598305").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 13:04
S36 3	2	("4994401").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/08/20 13:04
S36 4	439692	SiC "Si.sub."? "C.sub."? silicon adj carbide near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 10:29
S36 5	5855	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 10:29
S36 6	935	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near6 gate and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 10:30

S36 7	74	(SiC "Si.sub."? "C.sub."? silicon adj carbide) near4 gate and barrier and electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 13:17
S36 8	74	(SiC "Si.sub."? "C.sub."? silicon adj carbide "SiC.sub.2") near4 gate and barrier and electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 13:19
S36 9	0	"SiC.sub.2" near4 gate and barrier and electron adj affinity	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 13:20
S37 0	1	"SiC.sub.2" near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 13:20
S37 1	30	("SiC.sub.2" carbon near4 (doping doped dopant) near4 (silicon adj carbide SiC)) and gate and (transistor MOSFET MOS NMOS NMOSFET PMOSFET field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 14:44
S37 2	2	("6770918").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 15:01
S37 3	0	"SiC.sub.2" near6 gate adj insulat$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 15:02
S37 4	1	"SiC.sub.2" near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 15:02
S37 5	0	silicon adj dicarbide and gate and silicon adj dioxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 16:24
S37 6	8	("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:00

S37 7	1	first adj gate adj insulat$3 and second adj gate adj insulat$3 and "SiC.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 16:32
S37 8	1	first adj gate adj insulat$3 and second adj gate adj insulat$3 and (SiC2 "SiC.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 16:34
S37 9	38	barrier near4 silicon adj carbide same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 16:43
S38 0	0	(multiple adj gate adj insulat$3 adj (film layer)) near4 (silicon carbide silicon adj dicarbide SiC2 "Si C.sub.2" "SiC.sub.2")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 16:46
S38 1	7	("SiC.sub.2" SiC2 silicon adj dicarbide) and gate and silicon adj dioxide and "SiO.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:01
S38 2	340	"SiC.sub.2"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:01
S38 3	27	"SiC.sub.2" and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:01
S38 4	1	"SiC.sub.2" near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:02
S38 5	5	"SiC.sub.2" same gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:10
S38 6	2	("5369040").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:13

S387	2	"903452".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:14
S388	6	"256643".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:17
S389	7	"652068".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:17
S390	4	"652420".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:22
S391	3	"903486".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:25
S392	5	"259870".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 17:34
S393	5	"259870".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:25
S394	38	carbon adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:26
S395	7	carbon adj gate and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:28
S396	7	"carbon gate" and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:38

S39 7	0	carbon-gate near4 ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:38
S39 8	0	carbon-gate near4 pH-ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:38
S39 9	0	carbon near4 gate near4 pH-ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:39
S40 0	11	carbon near4 gate and pH-ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:40
S40 1	11	carbon near8 gate and pH-ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:40
S40 2	19	carbon and gate and pH-ISFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:42
S40 3	23145	(carbon C) near8 gate and (pH-ISFET MOSFET transistor CMOSFET MOS CMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:44
S40 4	51	carbon near8 gate and nanotube and field adj effect	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/24 18:44
S40 5	552	gate near4 (C carbon) near4 (silicon Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:04
S40 6	19	gate near4 (C carbon) near4 (silicon Si) near4 (doped doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:06

S40 7	19	gate near4 ("C" carbon) near4 (silicon Si) near4 (doped doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:10
S40 8	257	carbon near5 gate and ("257"/$9. ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:11
S40 9	161	carbon near3 gate and ("257"/$9. ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:15
S41 0	2	"5061976".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:13
S41 1	0	Si-doped near4 carbon near3 gate and ("257"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:16
S41 2	10	doped near4 carbon near3 gate and ("257"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:16
S41 3	2	(silicon si) near4 doped near4 carbon near3 gate and ("257"/$9. ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:17
S41 4	66958	silicon and (anneal annealing) carbon near3 gate and ("257"/$9. ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:18
S41 5	1	silicon and (anneal annealing) near4 carbon near4 gate and ("257"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:19
S41 6	4	silicon near4 (doped doping) near4 carbon near4 gate and ("257"/$9.ccls. "438"/$9.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:20

S41 7	7	silicon near4 (doped doping) near4 carbon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:25
S41 8	0	"C:Si" near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:25
S41 9	64	"C:Si"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:26
S42 0	7	"C:Si" and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:35
S42 1	4	"691004".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:36
S42 2	2	"903452".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:37
S42 3	4	"652420".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 13:37
S42 4	1	("5369040").PN.	USPAT; USOCR	OR	OFF	2004/09/25 14:17
S42 5	542	floating near2 gate and control near2 gate and ((Si silicon) near2 (C carbon) silicon adj carbide "Si. sub."$2"C.sub."$2 silicon-doped adj carbon carbon-doped adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 14:23
S42 6	151	floating near2 gate and control near2 gate and ((Si silicon) near2 (carbon) silicon adj carbide "Si. sub."$2"C.sub."$2 silicon-doped adj carbon carbon-doped adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 16:04

S42 7	2	("5801401").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 16:04

| S42 8 | 223 | (US-4893273-$ or US-4841349-$ or US-4769686-$ or US-4738729-$ or US-4657699-$ or US-4462150-$ or US-4460670-$ or US-6125062-$ or US-6002143-$ or US-5852306-$ or US-5449925-$ or US-6301162-$ or US-6222778-$ or US-4426764-$ or US-6562131-$ or US-6547877-$ or US-6562130-$ or US-6537371-$ or US-5030580-$ or US-5907775-$ or US-5886379-$ or US-5877041-$ or US-5846859-$ or US-5789276-$ or US-5786250-$ or US-5754477-$).did. or (US-5740104-$ or US-5714766-$ or US-5670790-$ or US-5654208-$ or US-5623442-$ or US-5604357-$ or US-5580380-$ or US-5562769-$ or US-5557114-$ or US-5530581-$ or US-5477485-$ or US-5455432-$ or US-5415126-$ or US-5407845-$ or US-5298796-$ or US-5293560-$ or US-5260593-$ or US-5235195-$ or US-5145741-$ or US-5111430-$ or US-5049950-$ or US-5672889-$ or US-5661312-$ or US-5539217-$ or US-5506421-$ or US-5465249-$ or US-5323040-$).did. or (US-4507673-$ or US-6018166-$ or US-5625217-$ or US-5061976-$ or US-4943838-$ or US-6309907-$ or US-4768072-$ or US-4451391-$ or US-6307775-$ or US-6351411-$ or US-5898197-$ or US-5508543-$ or US-5808336-$ or US-5866930-$ or US-5557122-$ or US-6034001-$ or US-5393999-$ or US-6383576-$ or US-6166319-$ or US-5734181-$ or US-5451798-$ or US-5369040-$ or US-5260560-$ or US-5159424-$ or US-5056897-$ or US-5039354-$ or US-4826778-$).did. or (US-5886368-$ or US-5719410-$ or US-5371383-$ or US-6365919-$ or US-6313482-$ or US-6306691-$ or US-6297521-$ or US-6249020-$ or US-6133587-$ or US-6121633-$ or US-6075259-$ or US-6049110-$ or US-6011279-$ or US-5798548-$ or US-6099574-$ or US-6093937-$ or US-6084248-$ or US-4473836-$ or US-4113515-$ or US-4849797-$ or US-6344663-$ or US-6180958-$ or US-6133120-$ or US-5989958-$ or US-5801401-$ or US-5629222-$ or US-5449941-$).did. or (US-6144581-$ or US-6130147-$ or US-6031263-$ or US-5976926-$ or US-5858811-$ or US-5698869-$ or US-4994401-$ or US-6166401-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/09/25 18:18 |

S42 9	47	control adj (gates gate) and floating adj (gates gate) near4 (silicon adj carbide "SiC")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:30
S43 0	2	"6309907".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:32
S43 1	2	("5886368").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:42
S43 2	3	"902843".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:49
S43 3	23	(("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:51
S43 4	25	(("4598305") or ("4980303") or ("4994401") or ("5189504") or ("5336361") or ("5367306") or ("5409501") or ("5990531") or ("6100193") or ("6166768") or ("6365919") or ("5471515")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 17:51
S43 5	1	"135413".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/25 18:19
S43 6	7	"134713".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/25 18:22
S43 7	33	"6031263"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/25 18:23
S43 8	2	("6031263").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:24

S43 9	2	("6307775").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:24
S44 0	2	("6249020").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:29
S44 1	16	(("5798548") or ("5808336") or ("5828101") or ("5861346") or ("5886376") or ("5976926") or ("5989958") or ("5990531") or ("6084248") or ("6093937") or ("6099574") or ("6100193") or ("6130147") or ("6166768") or ("6271566") or ("6365919")).PN.	USPAT; USOCR	OR	OFF	2004/09/25 18:34
S44 2	2	"902133".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:38
S44 3	6	(("5336361") or ("5990531") or ("6166768")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:05
S44 4	4	(("5910665") or ("6049091")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:55
S44 5	3	"231687".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 18:56

S44 6	233	(US-4598305-$ or US-5441901-$ or US-6108177-$ or US-5408377-$ or US-6205052-$ or US-6563260-$ or US-6514820-$ or US-6734510-$ or US-6731531-$ or US-6178112-$ or US-6236590-$ or US-6166948-$ or US-5793697-$ or US-5640343-$ or US-6197439-$ or US-6465375-$ or US-6452839-$ or US-6452831-$ or US-6723581-$ or US-6492694-$ or US-4189826-$ or US-4373167-$ or US-5932902-$ or US-6407426-$ or US-6297994-$ or US-6304493-$).did. or (US-6141260-$ or US-5910665-$ or US-5861346-$ or US-5336361-$ or US-6049091-$ or US-5828101-$ or US-5990531-$ or US-6100193-$ or US-6300193-$ or US-5886376-$ or US-5959896-$ or US-6407424-$ or US-6246606-$ or US-6746921-$ or US-6630375-$ or US-6140181-$ or US-6271566-$ or US-6166768-$ or US-5061976-$ or US-4943838-$ or US-6309907-$ or US-4768072-$ or US-4451391-$ or US-5580380-$ or US-5604357-$ or US-5623442-$ or US-5654208-$).did. or (US-5670790-$ or US-5714766-$ or US-6778441-$ or US-6781876-$ or US-6762068-$ or US-6794255-$ or US-5719410-$ or US-5371383-$ or US-6365919-$ or US-6313482-$ or US-6306691-$ or US-6297521-$ or US-6249020-$ or US-6133587-$ or US-6121633-$ or US-6075259-$ or US-6049110-$ or US-6011279-$ or US-5798548-$ or US-5672889-$ or US-5661312-$ or US-5539217-$ or US-5506421-$ or US-5465249-$ or US-5323040-$ or US-4507673-$ or US-6018166-$).did. or (US-5625217-$ or US-4849797-$ or US-6344663-$ or US-6180958-$ or US-6133120-$ or US-5989958-$ or US-5801401-$ or US-5629222-$ or US-5449941-$ or US-5393999-$ or US-6383576-$ or US-6166319-$ or US-5734181-$ or US-5451798-$ or US-5369040-$ or US-5260560-$ or US-5159424-$ or US-5056897-$ or US-5039354-$ or US-4826778-$ or US-5886368-$ or US-6099574-$ or US-6144581-$ or US-6166401-$ or US-5976926-$ or US-6031263-$ or US-6084248-$).did. or (US-6093937-$ or US-5858811-$ or US-5698869-$ or US-4113515-$ or US-4473836-$ or US-6163066-$ or US-6130147-$ or US-6573169-$	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/25 19:01

S44 7	0	carbon-doped near4 silicon near4 floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:01
S44 8	0	carbon near4 (doped dopant) near4 silicon near4 floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:03
S44 9	0	c-doped near4 silicon near4 floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:03
S45 0	2	("6746893").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:19
S45 1	2	("6762068").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:22
S45 2	2	("5949483").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:33
S45 3	0	micron.as. and floating.clm. and (reset control).clm. and "Si.sub."$2"C.sub."$2.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:35
S45 4	145	micron.as. and floating.clm. and (reset control).clm. and (silicon carbide "Si.sub."$2"C.sub."$2). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:36
S45 5	4	"902132".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:40

S45 6	5	"259870".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:45
S45 7	7	"138294".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 19:58
S45 8	2	("5886368").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 20:22
S45 9	0	("903453.ap.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 20:23
S46 0	3	"903453".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/25 20:23

| S46 1 | 233 | (US-6762068-$ or US-6778441-$ or US-6746893-$ or US-6746921-$ or US-6731531-$ or US-6734510-$ or US-6723581-$ or US-6630375-$ or US-6586797-$ or US-6573169-$ or US-6563260-$ or US-6547877-$ or US-6562130-$ or US-6537371-$ or US-6562131-$ or US-6492694-$ or US-6514820-$ or US-6452839-$ or US-6465375-$ or US-6383576-$ or US-6407424-$ or US-6407426-$ or US-6452831-$ or US-6351411-$ or US-6365919-$ or US-6344663-$).did. or (US-6309907-$ or US-6313482-$ or US-6307775-$ or US-6306691-$ or US-6297994-$ or US-6300193-$ or US-6301162-$ or US-6304493-$ or US-6249020-$ or US-6297521-$ or US-6205052-$ or US-6222778-$ or US-6236590-$ or US-6246606-$ or US-6180958-$ or US-6197439-$ or US-6794255-$ or US-6781876-$ or US-4738729-$ or US-4768072-$ or US-4507673-$ or US-4598305-$ or US-4657699-$ or US-4462150-$ or US-5056897-$ or US-4994401-$ or US-5039354-$).did. or (US-4473836-$ or US-4460670-$ or US-4113515-$ or US-4189826-$ or US-4373167-$ or US-4426764-$ or US-4451391-$ or US-6100193-$ or US-5990531-$ or US-6166768-$ or US-5336361-$ or US-6271566-$ or US-6049091-$ or US-5861346-$ or US-5828101-$ or US-5910665-$ or US-4849797-$ or US-4893273-$ or US-4769686-$ or US-4826778-$ or US-5030580-$ or US-4943838-$ or US-4841349-$ or US-5049950-$ or US-5623442-$ or US-5530581-$ or US-5539217-$).did. or (US-5557114-$ or US-5557122-$ or US-5506421-$ or US-5508543-$ or US-5455432-$ or US-5465249-$ or US-5477485-$ or US-5449941-$ or US-5451798-$ or US-5407845-$ or US-5408377-$ or US-5415126-$ or US-5441901-$ or US-5449925-$ or US-6099574-$ or US-6108177-$ or US-5369040-$ or US-5393999-$ or US-5371383-$ or US-5323040-$ or US-5298796-$ or US-5293560-$ or US-5260560-$ or US-5260593-$ or US-5159424-$ or US-5235195-$ or US-5145741-$).did. or (US-5061976-$ or US-5111430-$ or US-6133120-$ or US-5976926-$ or US-5907775-$ or US-5932902-$ or US-5852306-$ or US-5858811-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/09/27 07:36 |

S46 2	19	carbon near4 gate and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2004/09/27 08:18
S46 3	2	("6309907").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 08:26
S46 4	0	floating adj gate and control adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 08:31
S46 5	0	floating adj gate and silicon adj dioxide near3 (interlayer adj dielectric ild) and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 08:31
S46 6	34	floating adj gate and silicon adj dioxide and (interlayer adj dielectric ild) and mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 09:18
S46 7	4	"691004".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 10:54
S46 8	170	floating adj gate and control adj gate and (silicon adj carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 10:55
S46 9	47	floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eprom)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 11:05
S47 0	52	floating adj gate near4 (silicon adj carbide SiC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 11:05
S47 1	5	floating adj gate near4 (silicon adj carbide SiC) not (floating adj gate near4 (silicon adj carbide SiC) and control adj gate and (memory eprom))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 11:10

S47 2	2	"903452".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 11:11
S47 3	5	"746893".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 11:11
S47 4	2	"6746893".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:41
S47 5	0	eprom near5 (p-type n-type) near5 (preferabl$1 advantage$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:42
S47 6	5	floating adj gate near5 (p-type n-type) near5 (preferabl$1 advantage$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:44
S47 7	94	channel near5 (p-type n-type) near5 (preferabl$1 advantage$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:48
S47 8	23	channel near5 (p-type n-type) near5 (preferabl$1 advantage$3) and (eprom memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:57
S47 9	24	channel near5 (p-type n-type) near5 (preferabl$1 advantage$3) and (floating adj gate eprom memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 13:58
S48 0	7	channel near5 (p-type n-type) near5 (preferabl$1 advantage$3) and floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 14:03
S48 1	2	("4173766").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 14:06

S48 2	0	("floatingadjgateand(cmoscmosfet)").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 14:06
S48 3	478	floating adj gate.ti,ab,clm. and (cmos cmosfet).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:22
S48 4	2	("6731531").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:23
S48 5	4	"258467".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:24
S48 6	3	"903453".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:25
S48 7	5	"461593".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:27
S48 8	8	"789203".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/27 15:45
S48 9	9795	257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.$2.ccls.	US-PGPUB; USPAT	OR	OFF	2004/09/27 15:46
S49 0	1700	(257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.$2.ccls.) and floating adj gate near5 (sic silicon carbide "Si. sub."$3"C.sub."$3)	US-PGPUB; USPAT	OR	ON	2004/09/27 15:46
S49 1	36	(257/77.ccls. 257/314/ccls. 257/315.ccls. 257/316.ccls. 365/185.$2.ccls.) and floating adj gate near5 (sic silicon adj carbide "Si.sub."$3"C.sub."$3)	US-PGPUB; USPAT	OR	ON	2004/09/27 15:47

| S49 2 | 243 | (US-4852062-$ or US-6100193-$ or US-5990531-$ or US-6166768-$ or US-5336361-$ or US-6271566-$ or US-6049091-$ or US-5861346-$ or US-5828101-$ or US-5910665-$ or US-6703264-$ or US-6228751-$ or US-6141256-$ or US-6009018-$ or US-5754477-$ or US-5719410-$ or US-5670790-$ or US-5672889-$ or US-5698869-$ or US-5714766-$ or US-5640343-$ or US-5654208-$ or US-5661312-$ or US-5625217-$ or US-5629222-$ or US-5562769-$).did. or (US-5580380-$ or US-5604357-$ or US-5623442-$ or US-5530581-$ or US-5539217-$ or US-5557114-$ or US-5557122-$ or US-5789276-$ or US-5793697-$ or US-5734181-$ or US-5740104-$ or US-4189826-$ or US-4373167-$ or US-4426764-$ or US-4113515-$ or US-4657699-$ or US-4598305-$ or US-4460670-$ or US-4462150-$ or US-4473836-$ or US-4451391-$ or US-4826778-$ or US-4738729-$ or US-4768072-$ or US-4507673-$ or US-5506421-$ or US-5455432-$).did. or (US-5465249-$ or US-6108177-$ or US-5369040-$ or US-5393999-$ or US-5371383-$ or US-5323040-$ or US-5298796-$ or US-5293560-$ or US-5260560-$ or US-5260593-$ or US-5159424-$ or US-5235195-$ or US-5145741-$ or US-5061976-$ or US-5111430-$ or US-5049950-$ or US-5039354-$ or US-5056897-$ or US-5477485-$ or US-5449941-$ or US-5451798-$ or US-5407845-$ or US-5408377-$ or US-5415126-$ or US-5441901-$ or US-5449925-$ or US-6099574-$).did. or (US-5508543-$ or US-6011279-$ or US-5976926-$ or US-5907775-$ or US-5932902-$ or US-5959896-$ or US-5886368-$ or US-5886376-$ or US-5886379-$ or US-5898197-$ or US-5877041-$ or US-5852306-$ or US-5858811-$ or US-5866930-$ or US-5798548-$ or US-5808336-$ or US-5846859-$ or US-5786250-$ or US-6002143-$ or US-5989958-$ or US-6075259-$ or US-6031263-$ or US-6018166-$ or US-5030580-$ or US-4994401-$ or US-4943838-$ or US-4769686-$).did. or (US-4841349-$ or US-4849797-$ or US-4893273-$ or US-6133587-$ or US-6141260-$ or US-6144581-$ or US-6049110-$ or US-6034001-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2004/09/27 15:59 |

| S49 3 | 70 | ((US-4852062-$ or US-6100193-$ or US-5990531-$ or US-6166768-$ or US-5336361-$ or US-6271566-$ or US-6049091-$ or US-5861346-$ or US-5828101-$ or US-5910665-$ or US-6703264-$ or US-6228751-$ or US-6141256-$ or US-6009018-$ or US-5754477-$ or US-5719410-$ or US-5670790-$ or US-5672889-$ or US-5698869-$ or US-5714766-$ or US-5640343-$ or US-5654208-$ or US-5661312-$ or US-5625217-$ or US-5629222-$ or US-5562769-$).did. or (US-5580380-$ or US-5604357-$ or US-5623442-$ or US-5530581-$ or US-5539217-$ or US-5557114-$ or US-5557122-$ or US-5789276-$ or US-5793697-$ or US-5734181-$ or US-5740104-$ or US-4189826-$ or US-4373167-$ or US-4426764-$ or US-4113515-$ or US-4657699-$ or US-4598305-$ or US-4460670-$ or US-4462150-$ or US-4473836-$ or US-4451391-$ or US-4826778-$ or US-4738729-$ or US-4768072-$ or US-4507673-$ or US-5506421-$ or US-5455432-$).did. or (US-5465249-$ or US-6108177-$ or US-5369040-$ or US-5393999-$ or US-5371383-$ or US-5323040-$ or US-5298796-$ or US-5293560-$ or US-5260560-$ or US-5260593-$ or US-5159424-$ or US-5235195-$ or US-5145741-$ or US-5061976-$ or US-5111430-$ or US-5049950-$ or US-5039354-$ or US-5056897-$ or US-5477485-$ or US-5449941-$ or US-5451798-$ or US-5407845-$ or US-5408377-$ or US-5415126-$ or US-5441901-$ or US-5449925-$ or US-6099574-$).did. or (US-5508543-$ or US-6011279-$ or US-5976926-$ or US-5907775-$ or US-5932902-$ or US-5959896-$ or US-5886368-$ or US-5886376-$ or US-5886379-$ or US-5898197-$ or US-5877041-$ or US-5852306-$ or US-5858811-$ or US-5866930-$ or US-5798548-$ or US-5808336-$ or US-5846859-$ or US-5786250-$ or US-6002143-$ or US-5989958-$ or US-6075259-$ or US-6031263-$ or US-6018166-$ or US-5030580-$ or US-4994401-$ or US-4943838-$ or US-4769686-$).did. or (US-4841349-$ or US-4849797-$ or US-4893273-$ or US-6133587-$ or US-6141260-$ or US-6144581-$ or US-6049110-$ or US-6034001-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/09/27 15:59 |

S51 7	5	(("5,738,731") or ("6,177,706") or ("6,249,020")).PN.	USPAT; DERWENT	OR	OFF	2005/03/10 12:27
S51 8	4	S517 and ("si.sub."$4"c.sub."$4 "sic.sub."$4 "si.sub."$4c silicon carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 12:28
S51 9	3	S517 and ("si.sub."$4"c.sub."$4 "sic.sub."$4 "si.sub."$4c silicon adj carbide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:37
S52 0	4	"691004".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:50
S52 1	1451	("Si.sub."$4C "Si.sub."$4"C.sub. "$4 "SiC.sub."$4 (SiC silicon adj carbide) near10 C-doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:54
S52 2	118	("Si.sub."$4C "Si.sub."$4"C.sub. "$4 "SiC.sub."$4 (SiC silicon adj carbide) near10 C-doped) and transistor and gate.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 12:54
S52 3	6	("Si.sub."$4C "Si.sub."$4"C.sub. "$4 "SiC.sub."$4 (SiC silicon adj carbide) near10 C-doped) near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 13:04
S52 4	9	carbon near4 (doped dopant doping) near4 silicon near6 gate and (transistor MOS MOSFET).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 13:40
S52 5	11	((Si silicon) near2 gate near4 (C carbon) near2 (doped dopant)) ((C carbon) near2 gate near4 (Si silicon) near2 (doped dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:02
S52 6	37	((Si silicon poly-Si polysilicon) near2 gate near4 (C carbon) near2 (doped dopant)) ((C carbon) near2 gate near4 (Si silicon poly-Si polysilicon) near2 (doped dopant))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:25

| S527 | 247 | (US-20010032997-$ or
US-20010049183-$ or
US-20020006711-$ or
US-20020017647-$ or
US-20020024050-$ or
US-20020036331-$ or
US-20020041514-$ or
US-20020055204-$ or
US-20020061615-$ or
US-20020126536-$ or
US-20020130378-$ or
US-20020137284-$ or
US-20030001191-$ or
US-20030034495-$ or
US-20030042516-$ or
US-20030042527-$ or
US-20030042528-$ or
US-20030042532-$ or
US-20030043622-$ or
US-20030043630-$ or
US-20030043632-$ or
US-20030043633-$ or
US-20030043637-$ or
US-20030045082-$ or
US-20030048666-$ or
US-20030049900-$).did. or
(US-20030205754-$ or
US-20030234420-$ or
US-20030235081-$ or
US-20040079989-$ or
US-20040104426-$ or
US-20040159863-$ or
US-20040160830-$ or
US-20040164341-$ or
US-20040164342-$ or
US-20040168145-$ or
US-20040185630-$ or
US-20040023500-$ or
US-20020125479-$).did. or
(US-4113515-$ or US-4189826-$
or US-4373167-$ or US-4426764-$
or US-4451391-$ or US-4460670-$
or US-4462150-$ or US-4473836-$
or US-4507673-$ or US-4598305-$
or US-4657699-$ or US-4738729-$
or US-4768072-$ or US-4769686-$
or US-4826778-$ or US-4841349-$
or US-4849797-$ or US-4852062-$
or US-4893273-$ or US-4943838-$
or US-4994401-$ or US-5030580-$
or US-5039354-$ or US-5049950-$
or US-5056897-$ or
US-5061976-$).did. or
(US-5111430-$ or US-5145741-$
or US-5159424-$ or US-5235195-$
or US-5260560-$ or US-5260593-$
or US-5293560-$ or US-5298796-$
or US-5323040-$ or US-5336361-$
or US-5369040-$ or US-5371383-$
or US-5393999-$ or US-5407845-$ | US-PGPUB;
USPAT;
EPO; JPO;
DERWENT | OR | OFF | 2005/03/10 14:13 |

S528	2	S527 and hamakawa.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 14:15
S529	158	S527 and gate near4 (silicon adj carbide carbide silicon polysilicon carbon C Si poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 14:19
S530	3	("5189504").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 14:22
S531	2	jp-03181176$-$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 14:52
S532	151	("Si:C" "C:Si" near2 gate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:27
S533	0	("Si:C" "C:Si") near2 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:28
S534	1	("Si:C" "C:Si") near6 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:54
S535	2	("6492694").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 14:52
S536	1	("Si:C" "C:Si") near8 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:54
S537	1	("Si:C" "C:Si") near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 14:55

S53 8	22	("Si:C" "C:Si" carbon adj doped C-doped) near10 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 15:16
S53 9	48	carbon adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 15:17
S54 0	25	carbon adj gate and silicon near4 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/10 15:18
S54 1	2	("4852062").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/10 15:18

| S54 2 | 260 | (US-20010032997-$ or US-20010049183-$ or US-20020006711-$ or US-20020017647-$ or US-20020024050-$ or US-20020036331-$ or US-20020041514-$ or US-20020055204-$ or US-20020061615-$ or US-20020126536-$ or US-20020130378-$ or US-20020137284-$ or US-20030001191-$ or US-20030034495-$ or US-20030042516-$ or US-20030042527-$ or US-20030042528-$ or US-20030042532-$ or US-20030043622-$ or US-20030043630-$ or US-20030043632-$ or US-20030043633-$ or US-20030043637-$ or US-20030045082-$ or US-20030048666-$ or US-20030049900-$).did. or (US-20030205754-$ or US-20030234420-$ or US-20030235081-$ or US-20040079989-$ or US-20040104426-$ or US-20040159863-$ or US-20040160830-$ or US-20040164341-$ or US-20040164342-$ or US-20040168145-$ or US-20040185630-$ or US-20040023500-$ or US-20020125479-$ or US-20040217430-$ or US-20040262694-$ or US-20040253776-$).did. or (US-4113515-$ or US-4189826-$ or US-4373167-$ or US-4426764-$ or US-4451391-$ or US-4460670-$ or US-4462150-$ or US-4473836-$ or US-4507673-$ or US-4598305-$ or US-4657699-$ or US-4738729-$ or US-4768072-$ or US-4769686-$ or US-4826778-$ or US-4841349-$ or US-4849797-$ or US-4852062-$ or US-4893273-$ or US-4943838-$ or US-4994401-$ or US-5030580-$ or US-5039354-$ or US-5049950-$ or US-5056897-$ or US-5061976-$).did. or (US-5111430-$ or US-5145741-$ or US-5159424-$ or US-5235195-$ or US-5260560-$ or US-5260593-$ or US-5293560-$ or US-5298796-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2005/03/10 16:21 |

S54 3	108	S542 and floating near2 gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/10 16:29
S54 4	0	S543 and halvis.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/10 16:29
S54 5	1	S542 and halvis.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/03/10 16:29

| S54 6 | 260 | (US-20010032997-$ or US-20010049183-$ or US-20020006711-$ or US-20020017647-$ or US-20020024050-$ or US-20020036331-$ or US-20020041514-$ or US-20020055204-$ or US-20020061615-$ or US-20020125479-$ or US-20020126536-$ or US-20020130378-$ or US-20020137284-$ or US-20030001191-$ or US-20030034495-$ or US-20030042516-$ or US-20030042527-$ or US-20030042528-$ or US-20030042532-$ or US-20030043622-$ or US-20030043630-$ or US-20030043632-$ or US-20030043633-$ or US-20030043637-$ or US-20030045082-$ or US-20030048666-$).did. or (US-20030049900-$ or US-20030205754-$ or US-20030234420-$ or US-20030235081-$ or US-20040023500-$ or US-20040079989-$ or US-20040104426-$ or US-20040159863-$ or US-20040160830-$ or US-20040164341-$ or US-20040164342-$ or US-20040168145-$ or US-20040185630-$ or US-20040217430-$ or US-20040253776-$ or US-20040262694-$).did. or (US-4113515-$ or US-4189826-$ or US-4373167-$ or US-4426764-$ or US-4451391-$ or US-4460670-$ or US-4462150-$ or US-4473836-$ or US-4507673-$ or US-4598305-$ or US-4657699-$ or US-4738729-$ or US-4768072-$ or US-4769686-$ or US-4826778-$ or US-4841349-$ or US-4849797-$ or US-4852062-$ or US-4893273-$ or US-4943838-$ or US-4994401-$ or US-5030580-$ or US-5039354-$ or US-5049950-$ or US-5056897-$ or US-5061976-$).did. or (US-5111430-$ or US-5145741-$ or US-5159424-$ or US-5189504-$ or US-5235195-$ or US-5260560-$ or US-5260593-$ or US-5293560-$ | US-PGPUB; USPAT; EPO; JPO; DERWENT | OR | OFF | 2005/03/11 12:15 |

S54 7	5	(("5738731") or ("6177706") or ("6249020")).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/11 12:15